In the Claims:

Please amend the claims to read as follows:

1. (Currently amended) A power supply in which a feed voltage (U_s) is routed through at least one longitudinal branch to at least one output, the at least one branch having a disconnect fuse formed as a controlled semiconductor switch (SW1) and a monitoring unit (UWE) being set up to supply a disconnect signal (s1) to the semiconductor switch when there are changes in voltage or current beyond ~~pre-definable~~ pre-defined tolerances, wherein

at least one series circuit of an auxiliary semiconductor switch (H1A), likewise triggered by the monitoring unit (UWE) and a ballast resistor [[(R1A)]] RA1, is connected in parallel to the main semiconductor switch (SW1) and in the event of an overload absorbs a substantial portion of the overload current in the branch.

2. (Currently amended) The power supply as described in Claim 1, wherein the monitoring unit (UWE) is set up to keep the auxiliary semiconductor switch (H1A) at least ~~essentially~~ substantially disconnected during normal operation, but to switch it on in the event of an overload while simultaneously disconnecting the main semiconductor switch (SW1).

3. (Canceled)

4. (Currently amended) The power supply as described in Claim 1, wherein the pre-definable short-circuit current (I_{K1}) of the branch is essentially determined by the ballast resistor [[(R1A)]] RA1 and the feed voltage (U_s), so that [[R1A]] RA1 $\approx U_s/I_{K1}$.

5. (Previously presented) The power supply as described in Claim 1, wherein the semiconductor switches (SW1, H1A) are of the FET type.

6. (Original) The power supply as described in Claim 5, wherein the semiconductor switches (SW1, H1A) are of the self-locking FET type, the gate of the main semiconductor switch (SW1) being connected to the source and triggered by an output of the monitoring unit (UWE) via a Zener diode (ZD1) and the gate of the auxiliary semiconductor switch (H1A) being triggered directly by the same output.

7. (Currently amended) The power supply as described in Claim 1, wherein the ballast resistor [[(R1A)]] RA1 is formed as a composite carbon resistor.